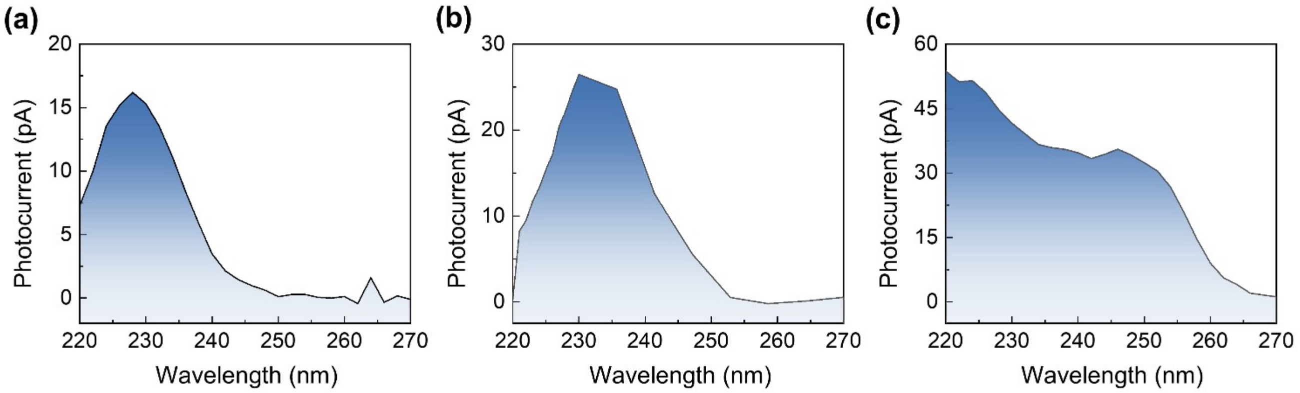

Fig. S1 Photocurrent versus incident wavelength curves for devices of different thicknesses at the same light intensity. (a) 13 nm Ga_2O_3-based device. (b) 75 nm Ga_2O_3-based device. (c) 160 nm Ga_2O_3-based device.

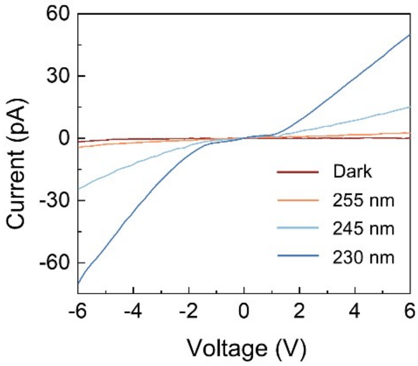

Fig. S2 I-V curves of 13 nm thick Ga2O3 under illumination at different wavelengths.